



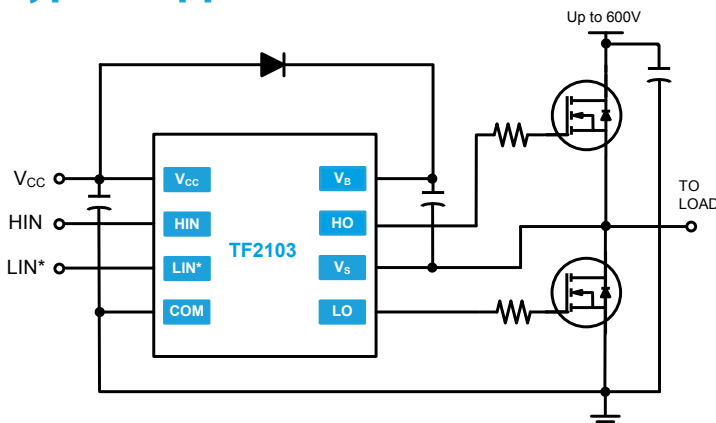
**Features**

- Floating high-side driver in bootstrap operation to 600V
- Drives two N-channel MOSFETs or IGBTs in a half bridge configuration
- 290mA source/600mA sink output current capability
- Outputs tolerant to negative transients
- Internal dead time of 520ns to protect MOSFETs
- Wide low side gate driver supply voltage: 10V to 20V
- Logic input (HIN and LIN\*) 3.3V capability
- Schmitt triggered logic inputs
- Undervoltage lockout for V<sub>cc</sub> (logic and low side supply)
- Extended temperature range: -40°C to +125°C

**Applications**

- DC-DC Converters
- AC-DC Inverters
- Motor Controls
- Class D Power Amplifiers

**Typical Application**



**Description**

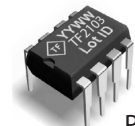
The TF2103 is a high voltage, high speed gate driver capable of driving N-channel MOSFETs and IGBTs in a half bridge configuration. Telefunken’s high voltage process enables the TF2103’s high side to switch to 600V in a bootstrap operation.

The TF2103 logic inputs are compatible with standard TTL and CMOS levels (down to 3.3V) to interface easily with controlling devices. The driver outputs feature high pulse current buffers designed for minimum driver cross conduction. TF2103 has a fixed internal deadtime of 520ns (typical).

The TF2103 is offered in PDIP-8 and SOIC-8(N) packages and operate over an extended -40 °C to +125 °C temperature range.



SOIC-8(N)

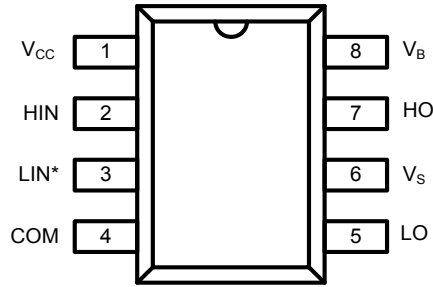


PDIP-8

**Ordering Information**

PART NUMBER	PACKAGE	PACK / Qty	MARK	
			Year	Week
TF2103-3AS	PDIP-8	Tube / 50	YYWW TF	TF2103 Lot ID
TF2103-TAU	SOIC-8(N)	Tube / 100	YYWW TF	TF2103 Lot ID
TF2103-TAH	SOIC-8(N)	T&R / 2500	YYWW TF	TF2103 Lot ID

**Pin Diagrams**



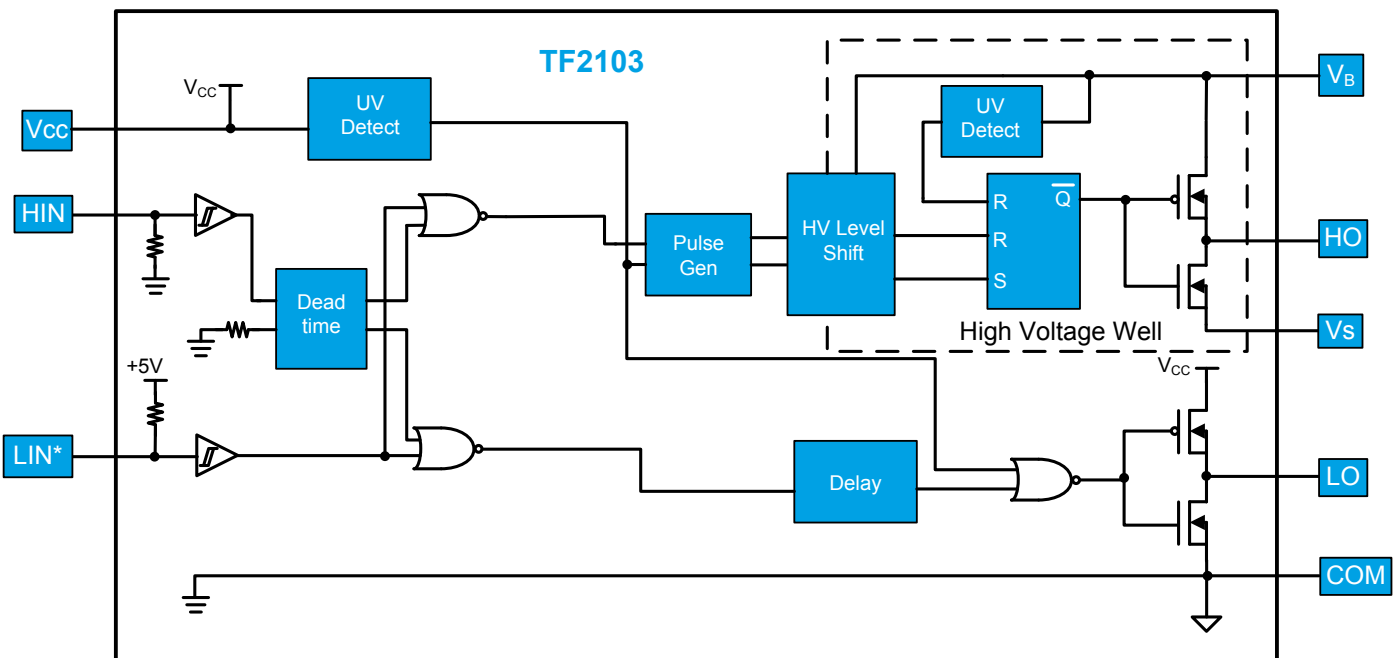
**Top View:** PDIP-8, SOIC-8

**Pin Descriptions**

**TF2103**

PIN NAME	PIN NUMBER	PIN DESCRIPTION
V <sub>CC</sub>	1	Logic and low side supply
HIN	2	Logic input for high-side gate driver output in phase with HO
LIN*	3	Logic input for low-side gate driver output out of phase with LO
COM	4	Low-side and logic return
LO	5	Low-side gate drive output
V <sub>S</sub>	6	High-side floating supply return
HO	7	High-side gate drive output
V <sub>B</sub>	8	High-side floating supply

**Functional Block Diagram**



## Absolute Maximum Ratings (NOTE1)

$V_B$  - High side floating supply voltage.....-0.3V to +624V  
 $V_S$  - High side floating supply offset voltage... $V_B$ -24V to  $V_B$ +0.3V  
 $V_{HO}$  - High side floating output voltage..... $V_S$ -0.3V to  $V_B$ +0.3V  
 $dV_S/dt$  - Offset supply voltage transient.....50V/ns

$V_{CC}$  - Low-side fixed supply voltage.....-0.3V to +24V  
 $V_{LO}$  - Low-side output voltage.....-0.3V to  $V_{CC}$ +0.3V  
 $V_{IN}$  - Logic input voltage (HIN and LIN\*).....-0.3V to  $V_{CC}$ +0.3V

**NOTE1** Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

$P_D$  - Package power dissipation at  $T_A \leq 25^\circ\text{C}$   
 SOIC-8.....0.625W  
 PDIP-8.....1.0W

SOIC-8(N) Thermal Resistance (NOTE2)

$\theta_{JA}$ .....200 °C/W

PDIP-8 Thermal Resistance (NOTE2)

$\theta_{JA}$ .....125 °C/W

$T_J$  - Junction operating temperature.....+150 °C

$T_L$  - Lead Temperature (soldering, 10 seconds).....+300 °C

$T_{stg}$  - Storage temperature .....-55 to 150 °C

**NOTE2** When mounted on a standard JEDEC 2-layer FR-4 board.

## Recommended Operating Conditions

Symbol	Parameter	MIN	MAX	Unit
$V_B$	High side floating supply absolute voltage	$V_S + 10$	$V_S + 20$	V
$V_S$	High side floating supply offset voltage	<b>NOTE3</b>	600	V
$V_{HO}$	High side floating output voltage	$V_S$	$V_B$	V
$V_{CC}$	Low side fixed supply voltage	10	20	V
$V_{LO}$	Low side output voltage	0	$V_{CC}$	V
$V_{IN}$	Logic input voltage (HIN and LIN*)	0	$V_{CC}$	V
$T_A$	Ambient temperature	-40	125	°C

**NOTE3** Logic operational for  $V_S$  of -5V to +600V. Logic state held for  $V_S$  of -5V to -VBS

**DC Electrical Characteristics** (NOTE4)
 $V_{BIAS} (V_{CC}, V_{BS}) = 15V, T_A = 25\text{ }^\circ\text{C}$ , unless otherwise specified.

Symbol	Parameter	Conditions	MIN	TYP	MAX	Unit
$V_{IH}$	Logic "1" (HIN) & Logic "0" (LIN*) input voltage	$V_{CC} = 10V \text{ to } 20V$	2.5			V
$V_{IL}$	Logic "0" (HIN) & Logic "1" (LIN*) input voltage				0.8	
$V_{OH}$	High level output voltage, $V_{BIAS} - V_O$	$I_O = 2mA$		0.05	0.2	
$V_{OL}$	Low level output voltage, $V_O$	$I_O = 2mA$		0.02	0.1	
$I_{LK}$	Offset supply leakage current	$V_B = V_S = 600V$			50	$\mu A$
$I_{BSQ}$	Quiescent $V_{BS}$ supply current	$V_{IN} = 0V \text{ or } 5V$		60	100	
$I_{CCQ}$	Quiescent $V_{CC}$ supply current	$V_{IN} = 0V \text{ or } 5V$		350	500	
$I_{IN+}$	Logic "1" input bias current	$HIN = 5V, LIN^* = 0V$		3	10	
$I_{IN-}$	Logic "0" input bias current	$HIN = 0V, LIN^* = 5V$			5	
$V_{CCUV+}$	$V_{CC}$ supply under-voltage positive going threshold		8.0	8.9	9.8	V
$V_{CCUV-}$	$V_{CC}$ supply under-voltage negative going threshold		7.4	8.2	9.0	
$I_{O+}$	Output high short circuit pulsed current	$V_O = 0V, PW \leq 10\ \mu s$	130	290		mA
$I_{O-}$	Output low short circuit pulsed current	$V_O = 15V, PW \leq 10\ \mu s$	270	600		

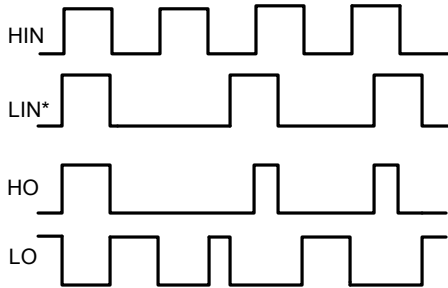
**NOTE4** The  $V_{IN}$ ,  $V_{TH}$ , and  $I_{IN}$  parameters are applicable to the two logic input pins: HIN and LIN\*. The  $V_O$  and  $I_O$  parameters are applicable to the respective output pins: HO and LO

**AC Electrical Characteristics**

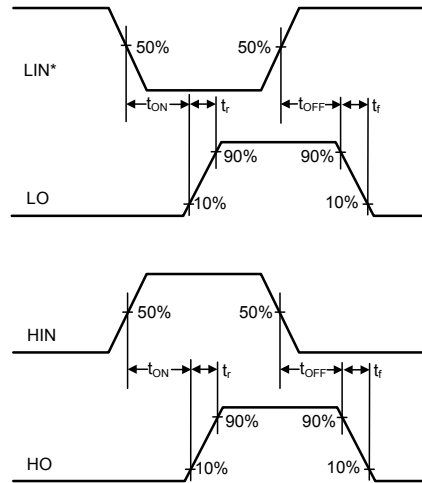
$V_{BIAS} (V_{CC}, V_{BS}) = 15V$ ,  $C_L = 1000pF$ , and  $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise specified.

Symbol	Parameter	Conditions	MIN	TYP	MAX	Unit
$t_{on}$	Turn-on propagation delay	$V_S = 0V$		680	820	ns
$t_{off}$	Turn-off propagation delay	$V_S = 600V$		150	220	
$t_{DM}$	Delay matching, HS & LS turn-on/turn-off				60	
$t_r$	Turn-on rise time	$V_S = 0V$		70	170	
$t_f$	Turn-off fall time			35	90	
$t_{DT}$	Deadtime: $t_{DT LO-HO}$ & $t_{DT HO-LO}$		400	520	650	

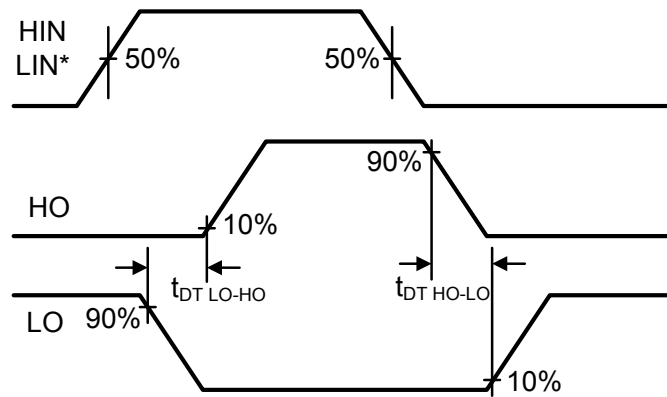
**Timing Waveforms**



**Figure 1.** Input / Output Timing Diagram



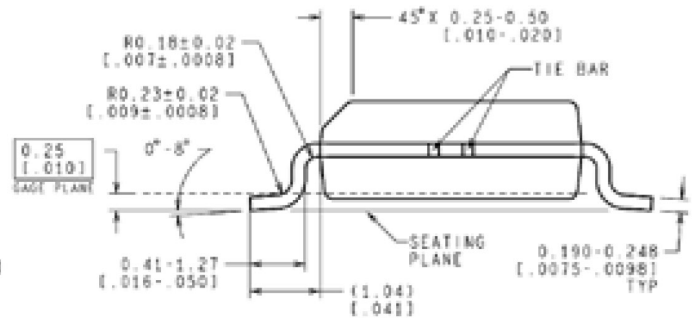
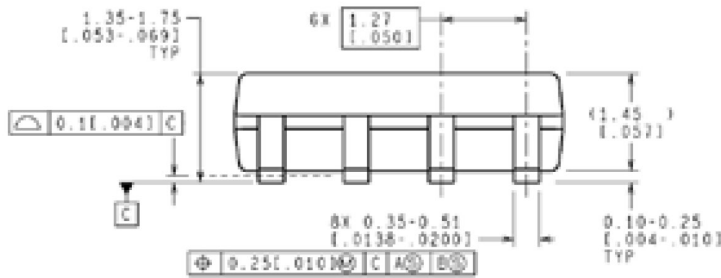
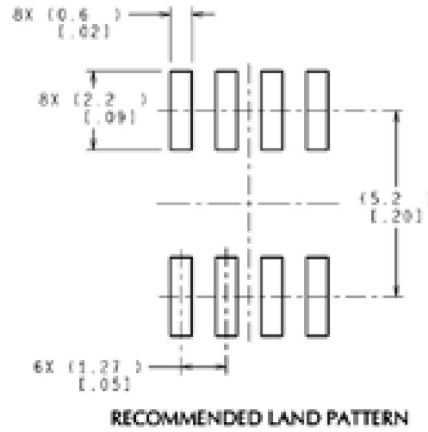
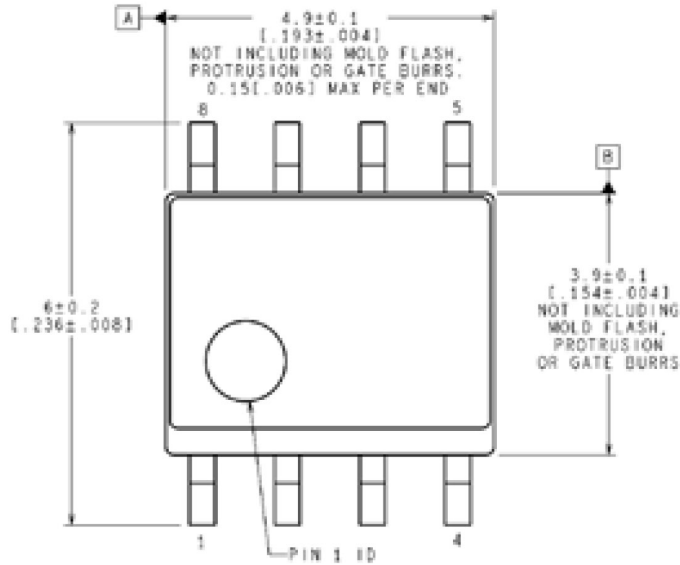
**Figure 2.** Switching Time Waveform Definitions



**Figure 3.** Deadtime Waveform Definitions

### Package Dimensions (SOIC-8 N)

Please contact support@telefunkensemi.com for package availability.



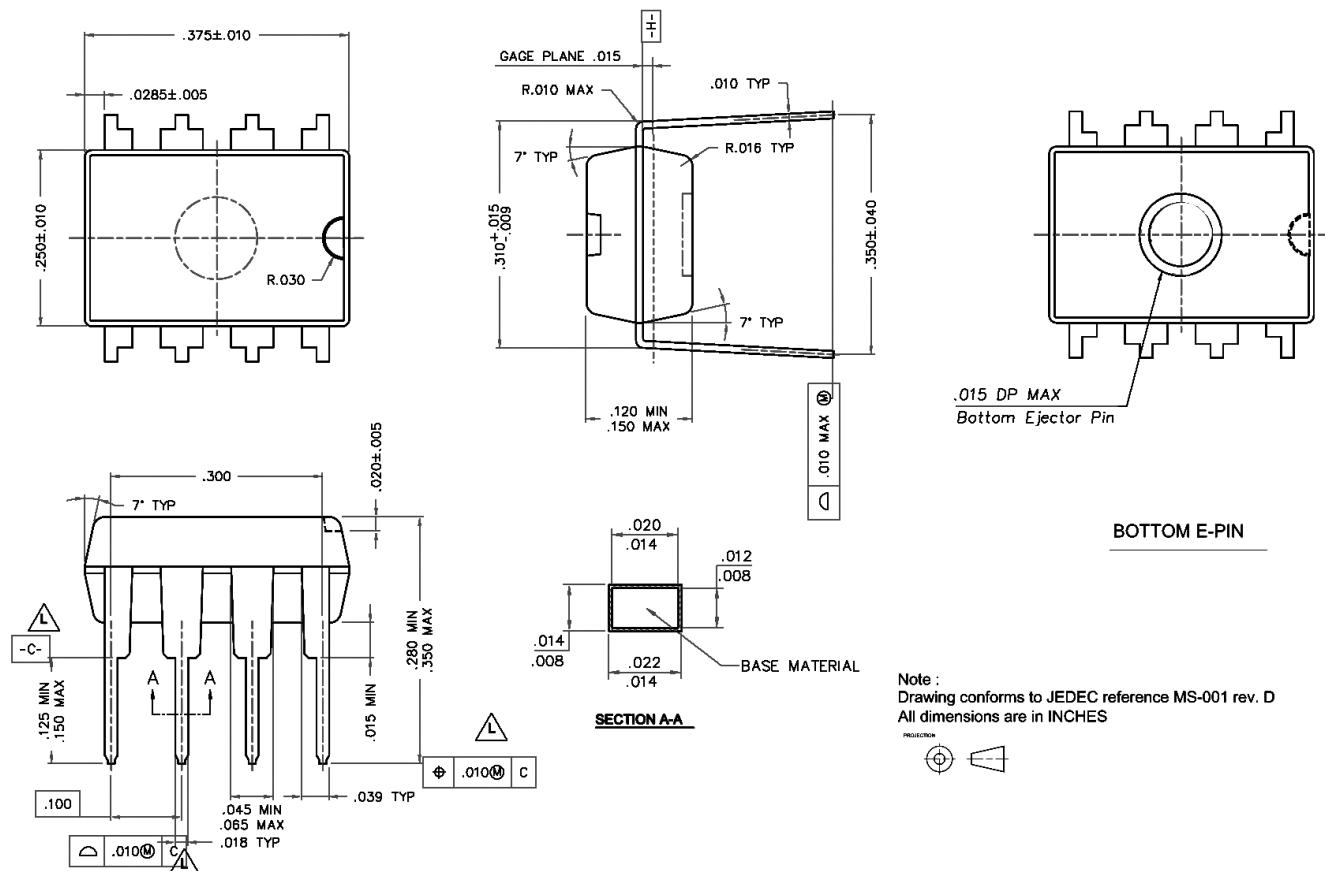
NOTES: UNLESS OTHERWISE SPECIFIED

1. REFERENCE JEDEC REGISTRATION MS-012, VARIATION AA.

CONTROLLING DIMENSION IS MILLIMETER  
VALUES IN [ ] ARE INCHES  
DIMENSIONS IN ( ) FOR REFERENCE ONLY

# Package Dimensions (PDIP-8)

Please contact support@telefunkensemi.com for package availability.



Note :  
Drawing conforms to JEDEC reference MS-001 rev. D  
All dimensions are in INCHES





## Notes

### Important Notice

TF Semiconductor Solutions (TFSS) PRODUCTS ARE NEITHER DESIGNED NOR INTENDED FOR USE IN MILITARY AND/OR AEROSPACE, AUTOMOTIVE OR MEDICAL DEVICES OR SYSTEMS UNLESS THE SPECIFIC TFSS PRODUCTS ARE SPECIFICALLY DESIGNATED BY TFSS FOR SUCH USE. BUYERS ACKNOWLEDGE AND AGREE THAT ANY SUCH USE OF TFSS PRODUCTS WHICH TFSS HAS NOT DESIGNATED FOR USE IN MILITARY AND/OR AEROSPACE, AUTOMOTIVE OR MEDICAL DEVICES OR SYSTEMS IS SOLELY AT THE BUYER'S RISK.

TFSS assumes no liability for application assistance or customer product design. Customers are responsible for their products and applications using TFSS products.

Resale of TFSS products or services with statements different from or beyond the parameters stated by TFSS for that product or service voids all express and any implied warranties for the associated TFSS product or service. TFSS is not responsible or liable for any such statements.

©2014 TFSS. All Rights Reserved. Information and data in this document are owned by TFSS wholly and may not be edited, reproduced, or redistributed in any way without the express written consent from TFSS.

For additional information please contact [support@tfsemi.com](mailto:support@tfsemi.com) or visit [www.tfsemi.com](http://www.tfsemi.com)